

Title (en)

Semiconductor device and method of manufacturing semiconductor device

Title (de)

Halbleiterbauelement und Verfahren zur Herstellung eines Halbleiterbauelements

Title (fr)

Dispositif à semi-conducteurs et procédé de fabrication de dispositif à semi-conducteurs

Publication

**EP 2262066 A3 20140319 (EN)**

Application

**EP 10164884 A 20100603**

Priority

JP 2009134281 A 20090603

Abstract (en)

[origin: EP2262066A2] A semiconductor device includes a semiconductor layer stacked on a substrate, a stripe-shaped ridge formed on a surface of the semiconductor layer, and electrode formed on an upper surface of the ridge and a protective film disposed on each side of the ridge. The electrode includes a flat portion having a flat surface substantially parallel to the upper surface of the ridge and sloped portions on both sides of the flat portion with each of the sloped portions having a sloped surface that is sloped with respect to the upper surface of the ridge. The protective film covers a region from a side surface of the ridge to the sloped surface of the sloped portion of the electrode.

IPC 8 full level

**H01S 5/22** (2006.01); **H01S 5/042** (2006.01)

CPC (source: EP US)

**H01S 5/04254** (2019.07 - EP US); **H01S 5/22** (2013.01 - EP US); **H01S 5/32341** (2013.01 - EP US); **H01S 5/0213** (2013.01 - EP US); **H01S 5/0218** (2013.01 - EP US); **H01S 5/04252** (2019.07 - EP US); **H01S 5/2205** (2013.01 - EP US); **H01S 2301/176** (2013.01 - EP US)

Citation (search report)

- [XAY] US 2004147094 A1 20040729 - HABERERN KEVIN WARD [US], et al
- [IY] US 2008073716 A1 20080327 - YAMAMOTO TSUYOSHI [JP], et al
- [A] US 5504768 A 19960402 - PARK CHAN-YONG [KR], et al
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CN110364928A; EP2369697B1; EP3217491A1

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO SE SI SK SM TR

Designated extension state (EPC)

BA ME RS

DOCDB simple family (publication)

**EP 2262066 A2 20101215**; **EP 2262066 A3 20140319**; **EP 2262066 B1 20170510**; DE 10164884 T1 20110421; EP 3217491 A1 20170913; EP 3217491 B1 20200610; JP 2011014891 A 20110120; JP 2015167263 A 20150924; JP 5824786 B2 20151202; JP 6094632 B2 20170315; US 2010308445 A1 20101209; US 2016197456 A1 20160707; US 9318874 B2 20160419; US 9692208 B2 20170627

DOCDB simple family (application)

**EP 10164884 A 20100603**; DE 10164884 T 20100603; EP 17168540 A 20100603; JP 2010126393 A 20100602; JP 2015131105 A 20150630; US 201615067724 A 20160311; US 79147410 A 20100601